UTCTIP110A PNPEXPITAXIAL PLANAR TRANSISTOR

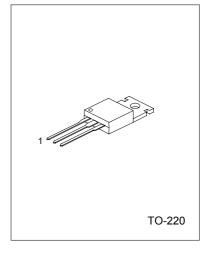
LOW SATURATION VOLTAGE PNP **DARLINGTON TRANSISTOR**

DESCRIPTION

The UTC TIP110A is designed for using in general purpose amplifier and switching applications.

FEATURE

*Low VCE(sat)



1:BASE 2:COLLECTOR 3:EMITTER

MAXIMUM RATINGS(Ta=25°C)

CHARACTERISTICS	SYMBOL	VALUE	UNITS
Collector Base Voltage	Vсво	40	V
Collector to Emitter Voltage	VCEO	30	V
Emitter To base Voltage	VEBO Sheet/III com	5	V
Collector Current	IC	10	Α
Junction Temperature	Tj	150(Max)	°C
Storage Temperature	Tstg	-55 ~ + 150	°C
Total Power Dissipations	PD	65	W

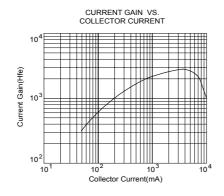
CHARACTERISTICS(Ta=25°C)

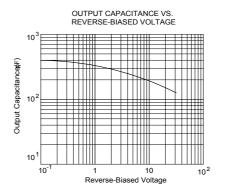
SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
BVCEO	Ic=100mA	30			V
Ісво	VCB=40V			1	μΑ
ICEO	VCE=20V			1	μΑ
IEBO	VEB=5V			100	nA
VCE(SAT)	IC=10A,IB=10mA			2.0	V
VBE(ON)	IC=5mA,VCE=2.0V			2.0	V
hFE1	IC=500mA,VCE=2.0V	2		60	K
hFE2	IC=10A,VCE=2.0V	1	20	60	K

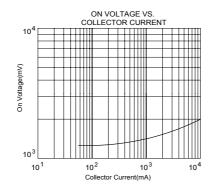
^{*}High current gain

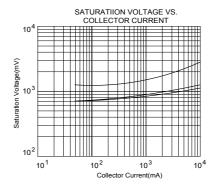
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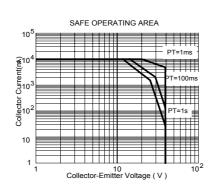
TYPICAL PERFORMANCE CHARACTERISTICS

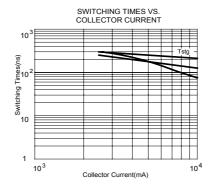












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UTCTIP110A PNPEXPITAXIAL PLANAR TRANSISTOR

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